

# FDMC4435BZ

## P-Channel Power Trench® MOSFET

### -30V, -18A, 20.0mΩ

#### Features

- Max  $r_{DS(on)}$  = 20.0mΩ at  $V_{GS} = -10V$ ,  $I_D = -8.5A$
- Max  $r_{DS(on)}$  = 37.0mΩ at  $V_{GS} = -4.5V$ ,  $I_D = -6.3A$
- Extended  $V_{GSS}$  range (-25V) for battery applications
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability
- HBM ESD protection level >7kV typical (Note 4)
- 100% UIL Tested
- Termination is Lead-free and RoHS Compliant

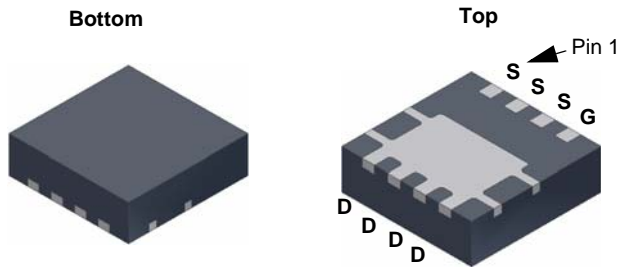


#### General Description

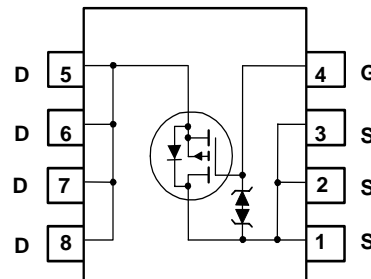
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

#### Applications

- High side in DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook



Power 33



#### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Ratings	Units
$V_{DS}$	Drain to Source Voltage		-30	V
$V_{GS}$	Gate to Source Voltage		$\pm 25$	V
$I_D$	Drain Current -Continuous (Package limited)	$T_C = 25^\circ\text{C}$	-18	A
	-Continuous (Silicon limited)	$T_C = 25^\circ\text{C}$	-31	
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	-8.5	
	-Pulsed		-50	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	24	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	31	W
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +150	$^\circ\text{C}$

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	53	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC4435BZ	FDMC4435BZ	Power 33	13"	12mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		22		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{V}$ , $V_{GS} = 0\text{V}$ , $T_J = 125^\circ\text{C}$			-1 -100	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 25\text{V}$ , $V_{DS} = 0\text{V}$			$\pm 10$	$\mu\text{A}$

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = -250\mu\text{A}$	-1.0	-1.9	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-5.3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10\text{V}$ , $I_D = -8.5\text{A}$		14.6	20.0	m $\Omega$
		$V_{GS} = -4.5\text{V}$ , $I_D = -6.3\text{A}$		23.1	37.0	
		$V_{GS} = -10\text{V}$ , $I_D = -8.5\text{A}$ , $T_J = 125^\circ\text{C}$		20.7	28.0	
$g_{FS}$	Forward Transconductance	$V_{DD} = -5\text{V}$ , $I_D = -8.5\text{A}$		24		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		1540	2045	pF
$C_{oss}$	Output Capacitance			295	395	pF
$C_{rss}$	Reverse Transfer Capacitance			260	385	pF
$R_g$	Gate Resistance		$f = 1\text{MHz}$		5.1	

### Switching Characteristics

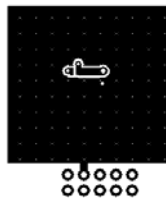
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{V}$ , $I_D = -8.5\text{A}$ , $V_{GS} = -10\text{V}$ , $R_{GEN} = 6\Omega$		10	20	ns	
$t_r$	Rise Time			6	12	ns	
$t_{d(off)}$	Turn-Off Delay Time			34	55	ns	
$t_f$	Fall Time			20	36	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{V}$ to $-10\text{V}$		33	46	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V}$ to $-4.5\text{V}$	$V_{DD} = -15\text{V}$ , $I_D = -8.5\text{A}$		17	24	nC
$Q_{gs}$	Gate to Source Charge				5		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				9		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = -8.5\text{A}$ (Note 2)		0.92	1.5	V
		$V_{GS} = 0\text{V}$ , $I_S = -1.9\text{A}$ (Note 2)		0.75	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = -8.5\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		22		ns
$Q_{rr}$	Reverse Recovery Charge			11		nC

#### NOTES:

1:  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $53^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty cycle < 2.0%.

3: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1\text{mH}$ ,  $I_{AS} = -7\text{A}$ ,  $V_{DD} = -27\text{V}$ ,  $V_{GS} = -10\text{V}$ .

4: The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

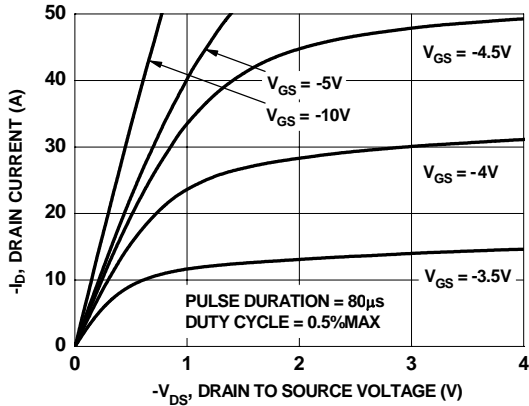


Figure 1. On-Region Characteristics

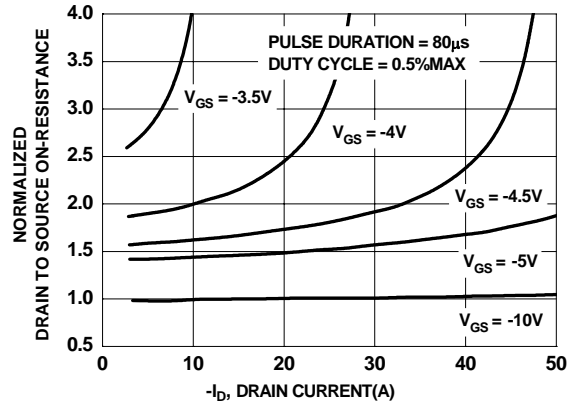


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

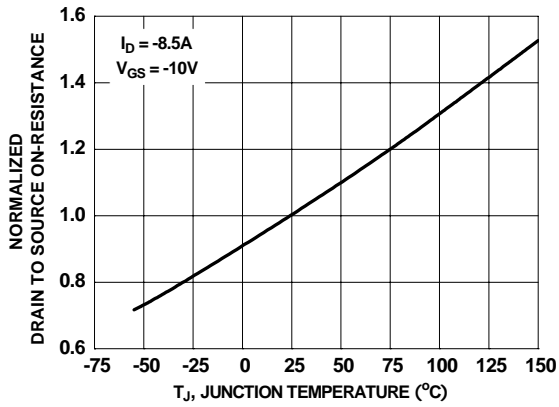


Figure 3. Normalized On-Resistance vs Junction Temperature

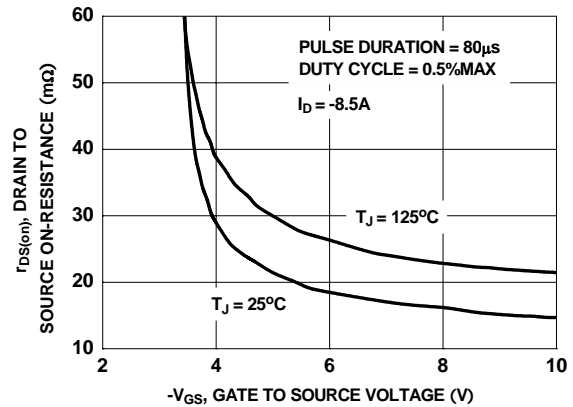


Figure 4. On-Resistance vs Gate to Source Voltage

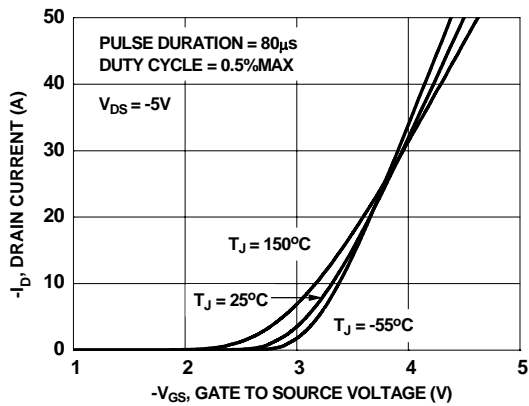


Figure 5. Transfer Characteristics

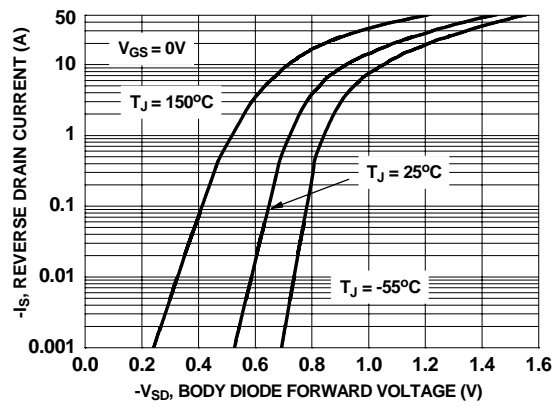
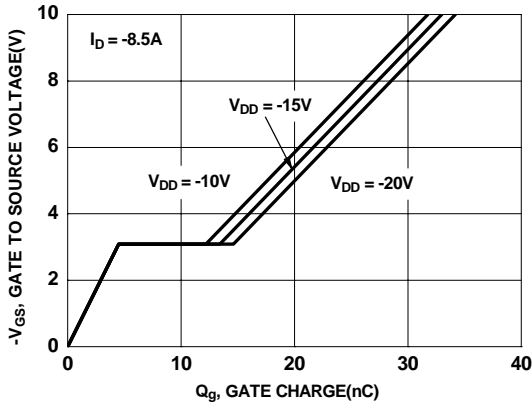
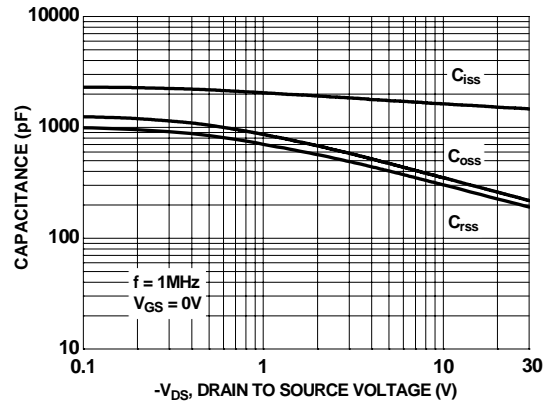


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

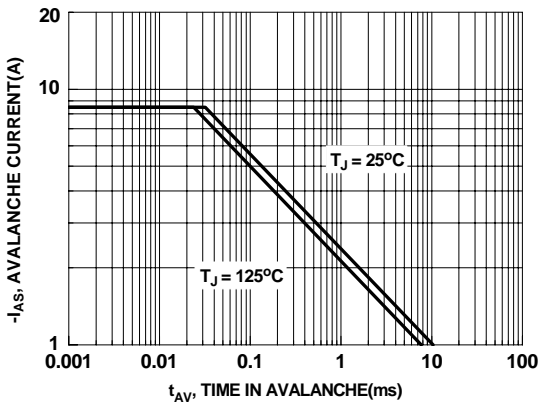
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



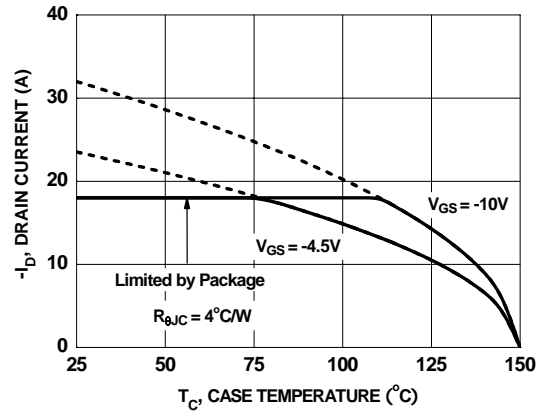
**Figure 7. Gate Charge Characteristics**



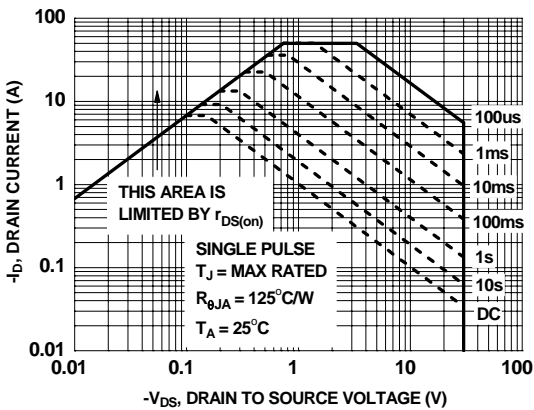
**Figure 8. Capacitance vs Drain to Source Voltage**



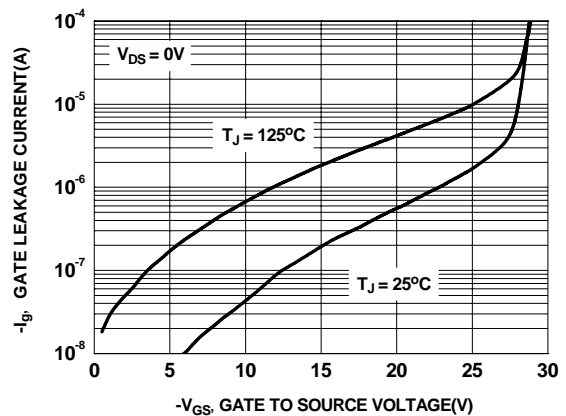
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

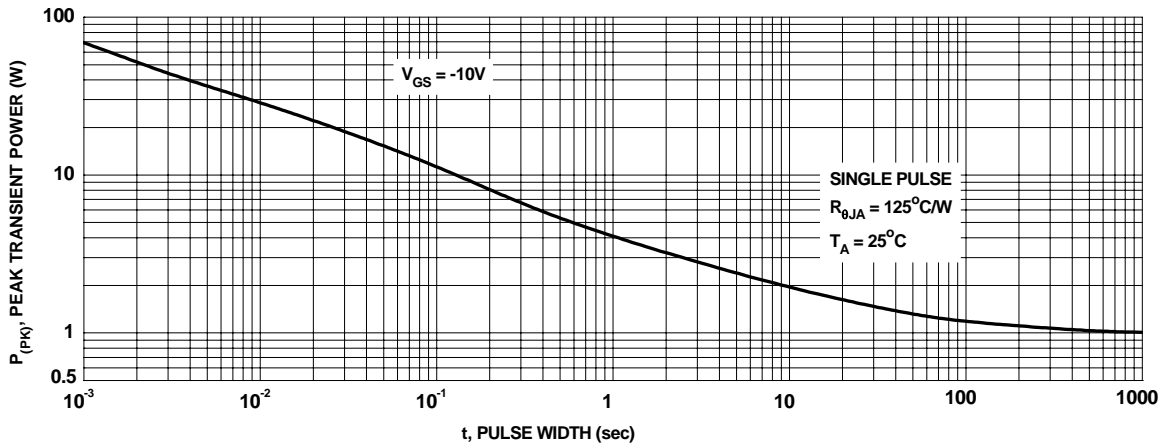


**Figure 11. Forward Bias Safe Operating Area**

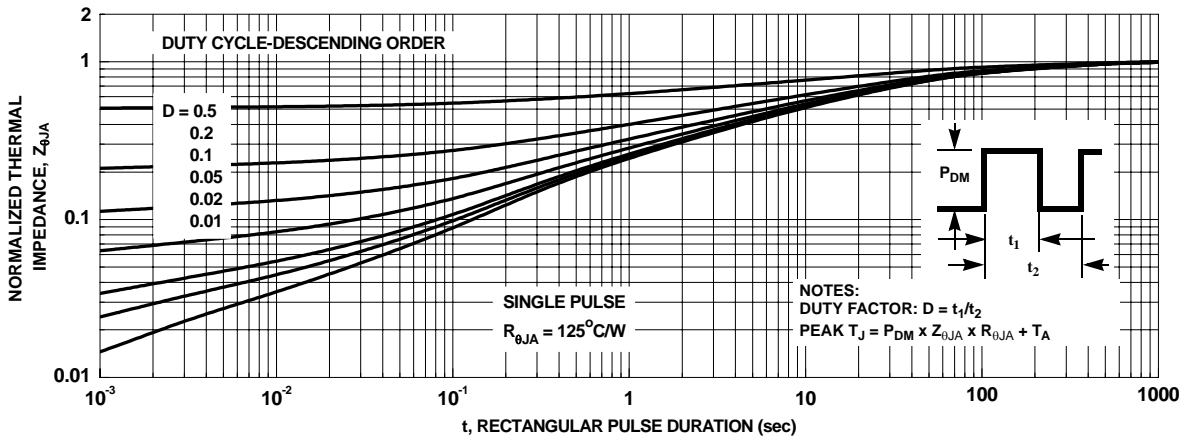


**Figure 12.  $I_{gss}$  vs  $V_{gss}$**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 13. Single Pulse Maximum Power Dissipation**








**Figure 14. Transient Thermal Response Curve**





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